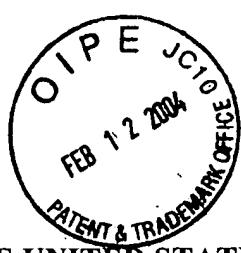


S/N 10/028643



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al. Examiner: Long Pham
Serial No.: 10/028,643 Group Art Unit: 2814
Filed: December 20, 2001 Docket: 1303.030US1
Title: LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO₃
GATE DIELECTRICS

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. § 1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

INFORMATION DISCLOSURE STATEMENT

Serial No :10/028643

Filing Date: December 20, 2001

Title: LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO₃ GATE DIELECTRICS

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Dkt: 1303.030US1

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 373-6944

Date 2-10-07

By 

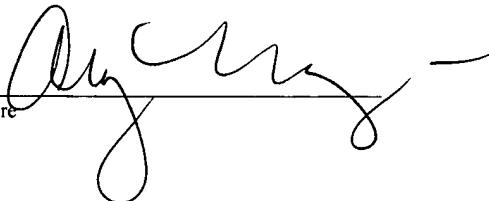
David C. Peterson
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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 10th day of February, 2004.

Name

Amy Moriarty

Signature



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STATEMENT BY APPLICANT**

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Complete if Known

Application Number	10/028,643
Filing Date	December 20, 2001
First Named Inventor	Ahn, Kie
Group Art Unit	2814
Examiner Name	Pham, Long

Attorney Docket No: 1303.030US1

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DATE CONSIDERED

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 600. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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Application Number	10/028,643
Filing Date	December 20, 2001
First Named Inventor	Ahn, Kie
Group Art Unit	2814
Examiner Name	Pham, Long

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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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Substitute Disclosure Statement Form (PTO-1449)

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Application Number	10/028,643
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Group Art Unit	2814
Examiner Name	Pham, Long

Attorney Docket No: 1303.030US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

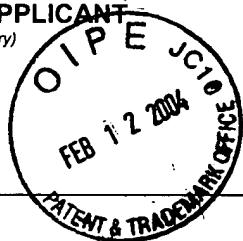
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Substitute Disclosure Statement Form (PTO-1449)

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <small>(Use as many sheets as necessary)</small>		Complete if Known <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%;">Application Number</td> <td>10/028,643</td> </tr> <tr> <td>Filing Date</td> <td>December 20, 2001</td> </tr> <tr> <td>First Named Inventor</td> <td>Ahn, Kie</td> </tr> <tr> <td>Group Art Unit</td> <td>2814</td> </tr> <tr> <td>Examiner Name</td> <td>Pham, Long</td> </tr> </table>		Application Number	10/028,643	Filing Date	December 20, 2001	First Named Inventor	Ahn, Kie	Group Art Unit	2814	Examiner Name	Pham, Long
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Group Art Unit	2814												
Examiner Name	Pham, Long												
<small>Sheet 4 of 4</small>		Attorney Docket No: 1303.030US1											



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